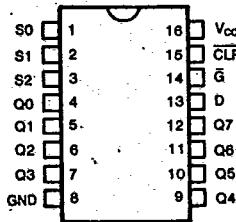


**KS54HCTLs 259
KS74HCTLs**

T-4607-05

8-Bit Addressable Latches**FEATURES**

- 8-Bit parallel-out storage register performs serial-to-parallel conversion with storage
- Asynchronous parallel clear
- Active high decoder
- Enable/Disable input simplifies expansion
- Expandable for N-bit applications
- Four distinct functional modes
- Function, pin-out, speed and drive compatibility with 54/74LS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:
 $I_{OL} = 8 \text{ mA} @ V_{OL} = 0.5V$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS74HCTLs: -40°C to $+85^{\circ}\text{C}$
KS54HCTLs: -55°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

PIN CONFIGURATION**FUNCTION TABLE**

Inputs	Output of Addressed Latch	Each Other Output	Function
CLR G			
H L	D	Q_{10}	Addressable Latch
H H	Q_{10}	Q_{10}	Memory
L L	D	L	8-Line Demultiplexer
L H	L	L	Clear

D = the level at the data input.
 Q_{10} = the level of Q_i ($i = 0, 1, \dots, 7$, as appropriate) before the indicated steady-state input conditions were established.

DESCRIPTION

The '259 is a high-speed addressable latch designed for general purpose storage applications in digital systems. It can be used for implementing working registers, serial-holding registers and active-high decoders or demultiplexers.

The '259 has four distinct modes of operation that are selected via the clear (CLR) and enable (G) inputs: 1) addressable latch; 2) memory; 3) active-high eight-channel demultiplexer; and 4) clear.

In the addressable latch mode, data on the data input (D) is written into the addressed latch. In this mode, data will be written into the addressed latch with all non-addressed latches remaining in their previous states.

In the memory mode, all latches remain in their previous state and are unaffected by the data of address inputs.

In the demultiplexing mode, addressed outputs will follow the state of the D input and all other outputs will remain low.

In the clear mode, all outputs are low and unaffected by the address and data inputs.

These devices provide speeds and drive capability equivalent to their LSSTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to Vcc and ground.

LATCH SELECTION TABLE

Select Inputs			Latch Addressed
S2	S1	S0	
L	L	L	0
L	L	H	1
L	H	L	2
L	H	H	3
H	L	L	4
H	L	H	5
H	H	L	6
H	H	H	7



SAMSUNG SEMICONDUCTOR

KS54HCTLs 259
KS74HCTLs

8-Bit Addressable Latches

T-46-07-05

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	$T_a=25^\circ C$	KS74HCTLs		KS54HCTLs		Unit
			Typ	$T_a = -40^\circ C$ to $+85^\circ C$		$T_a = -55^\circ C$ to $+125^\circ C$		
Minimum High-Level Input Voltage	V_{IH}			2.0		2.0		2.0
Maximum Low-Level Input Voltage	V_{IL}			0.8		0.8		0.8
Minimum High-Level Output Voltage	V_{OH}	$V_{IN}=V_{IH}$ or V_{IL} $I_o=-20\mu A$ $I_o=-4mA$	V_{CC} 4.2	$V_{CC}-0.1$ 3.98		$V_{CC}-0.1$ 3.84		$V_{CC}-0.1$ 3.7
Maximum Low-Level Output Voltage	V_{OL}	$V_{IN}=V_{IH}$ or V_{IL} $I_o=20\mu A$ $I_o=4mA$ $I_o=8mA$	0	0.1 0.26 0.39		0.1 0.33 0.5		0.1 0.4
Maximum Input Current	I_{IN}	$V_{IN}=V_{CC}$ or GND		± 0.1		± 1.0		± 1.0
Maximum Quiescent Supply Current	I_{CC}	$V_{IN}=V_{CC}$ or GND $I_{OUT}=0\mu A$		8.0		80.0		160.0
Additional Worst Case Supply Current	ΔI_{CC}	per input pin $V_i=2.4V$ other inputs: at V_{CC} or GND $I_{OUT}=0\mu A$		2.7		2.9		3.0

AC ELECTRICAL CHARACTERISTICS (Input t_i , $t_i \leq 6$ ns), HCTLs259

Characteristic	Symbol	Conditions [†]	$T_a=25^\circ C$	KS74HCTLs		KS54HCTLs		Unit
			V _{CC} =5.0V	$T_a = -40^\circ C$ to $+85^\circ C$	V _{CC} =5.0V $\pm 10\%$	$T_a = -55^\circ C$ to $+125^\circ C$	V _{CC} =5.0V $\pm 10\%$	
Maximum Propagation Delay CLR to any Q	t_{PHL}	$C_L=50pF$	22	30	37	45		ns
	t_{PLH}		20	27	34	41		ns
	t_{PLH}		20	27	34	41		ns
	t_{PLH}		26	34	43	51		ns
	t_{PHL}		26	34	43	51		ns
	t_{PLH}		22	30	37	45		ns
	t_{PHL}		22	30	37	45		ns
	t_{PLH}		8	10	13	15		ns
	t_w		8	10	13	15		ns
	t_{Gt}		8	10	13	15		ns
Minimum Pulse Width.	\overline{CLR} LOW							
	\overline{G} Low							
Minimum Setup Time,	t_{SU}							
Data or Address before \overline{Gt}								
Minimum Hold Time,	t_h							
Data or Address before \overline{Gt}								
Maximum Input Capacitance	C_{IN}							pF
Power Dissipation Capacitance*	C_{PD}							pF

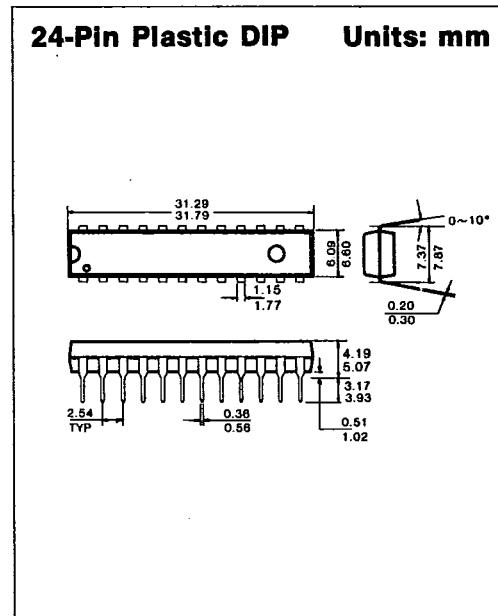
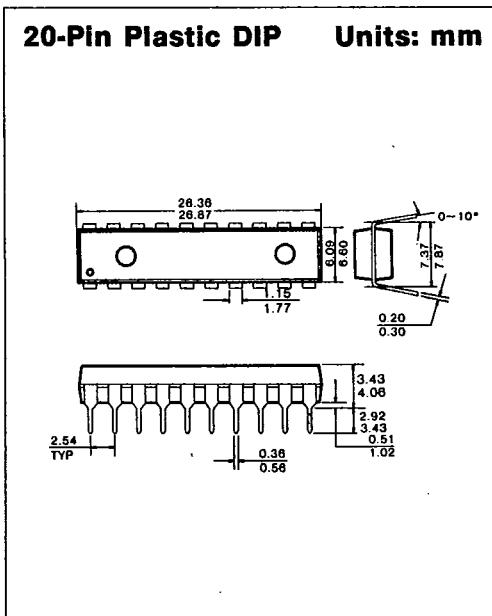
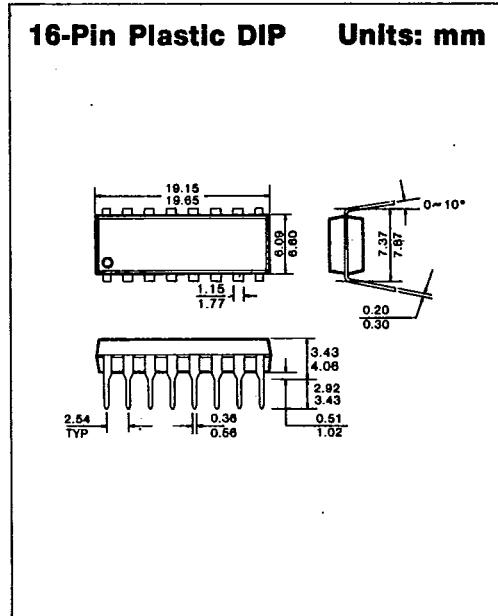
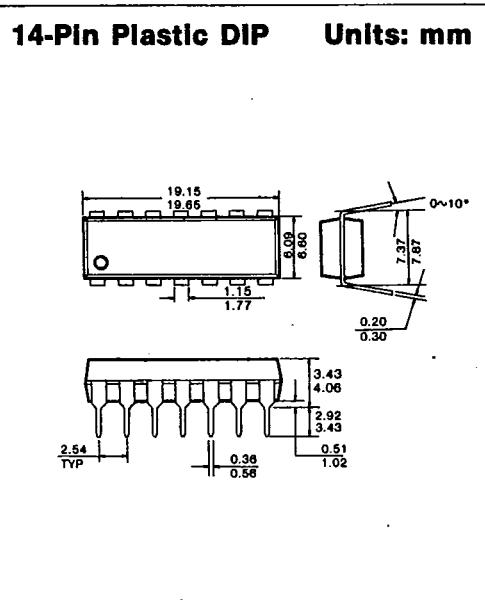
* C_{PD} determines the no-load dynamic power dissipation: $P_D=C_{PD}V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.



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PACKAGE DIMENSIONS**T-90-20****1. PLASTIC PACKAGES**

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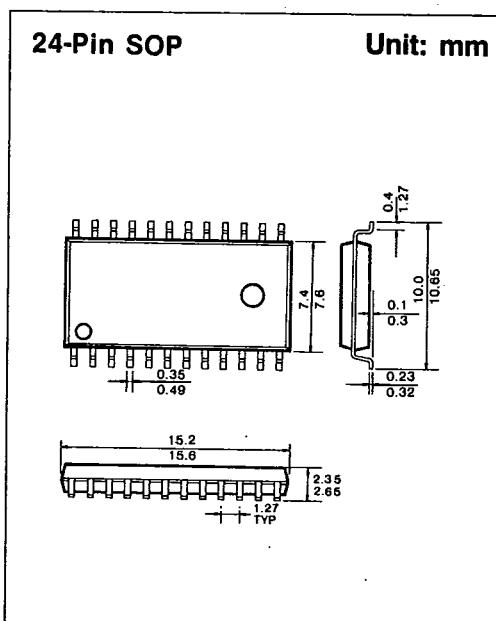
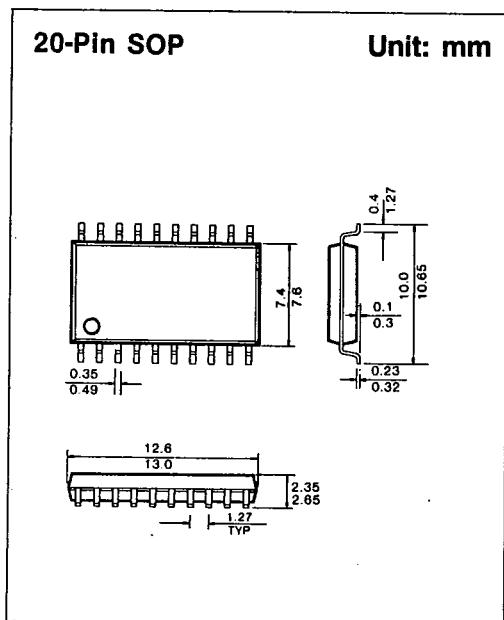
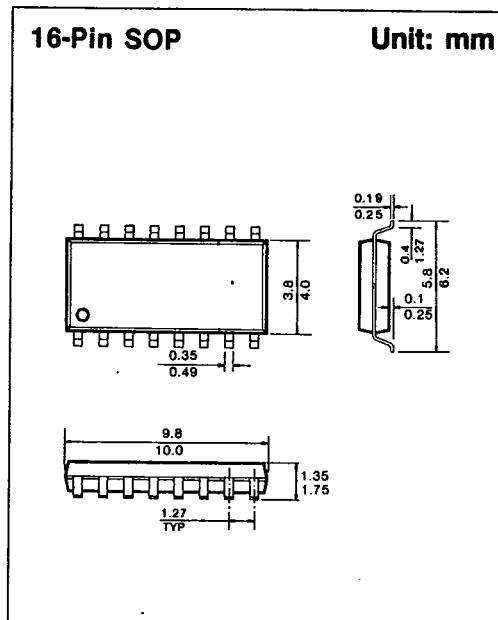
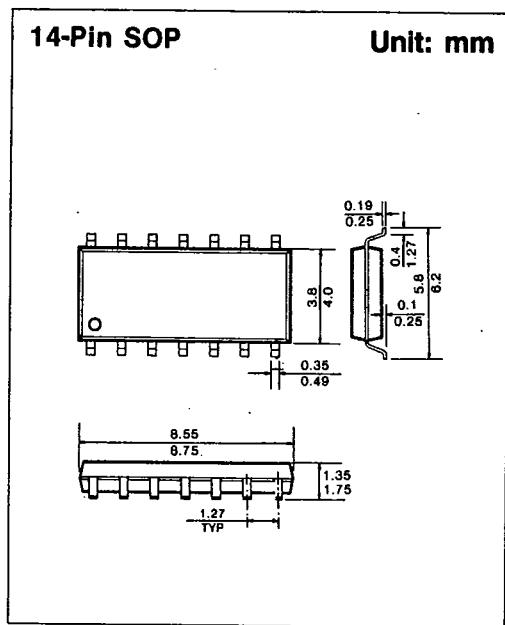


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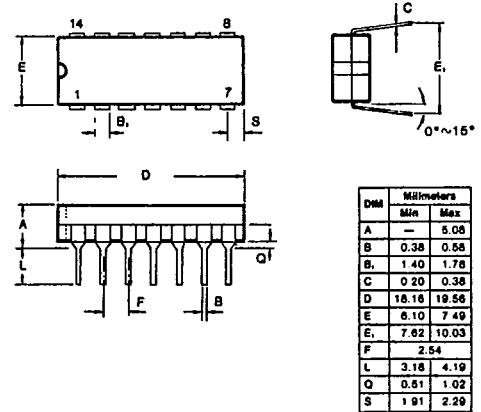
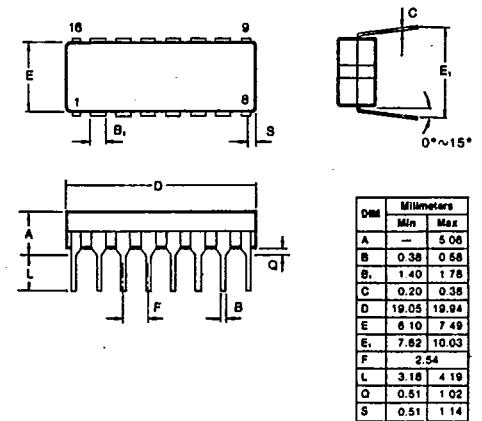
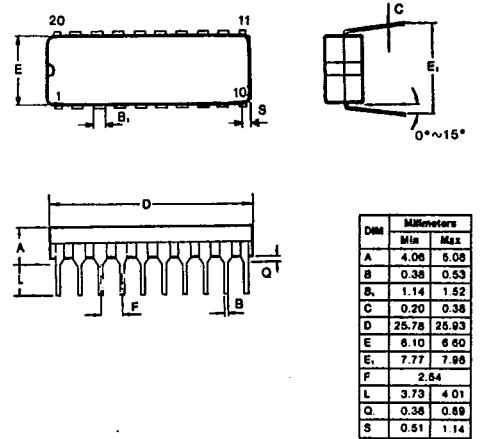
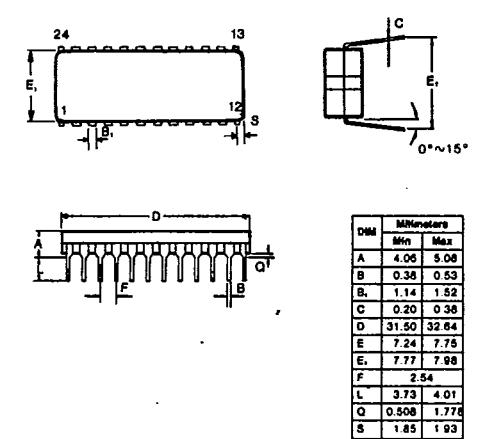
PACKAGE DIMENSIONS**T-90-20**

SAMSUNG SEMICONDUCTOR

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PACKAGE DIMENSIONST-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

7